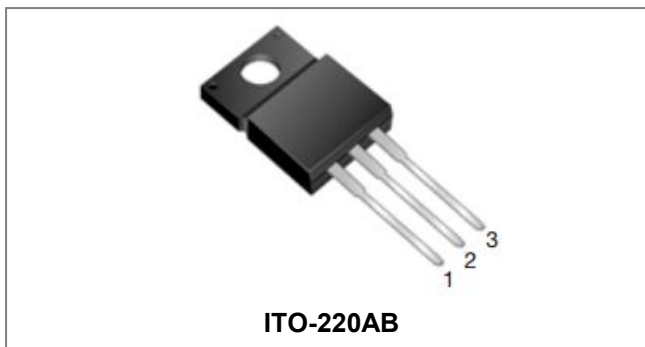


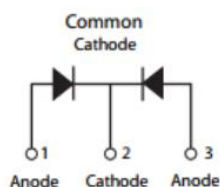
MURF2020CT ULTRAFAST RECTIFIER



Features

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=85^\circ\text{C}$, rectangular wave form	$\frac{10(\text{Per Leg})}{20(\text{Per Device})}$	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I_{FSM}	8.3ms, Half Sine pulse	100	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V_{F1}	@ 10A, Pulse, $T_J = 25^\circ\text{C}$	0.96	1.2	V
	V_{F2}	@ 10A, Pulse, $T_J = 125^\circ\text{C}$	0.73	1.0	V
Reverse Current(Per Leg)*	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.01	10	μA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	0.1	100	μA
Reverse Recovery Time(Per Leg)	t_{rr}	@ $I_F=500\text{mA}, I_R=1\text{A}, \text{ and } I_{rm}=250\text{mA}$	31	35	ns

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves

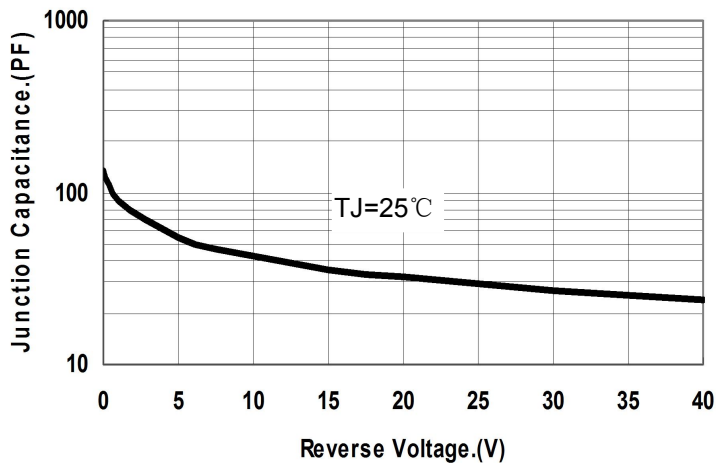


Fig.1-Typical Junction Capacitance

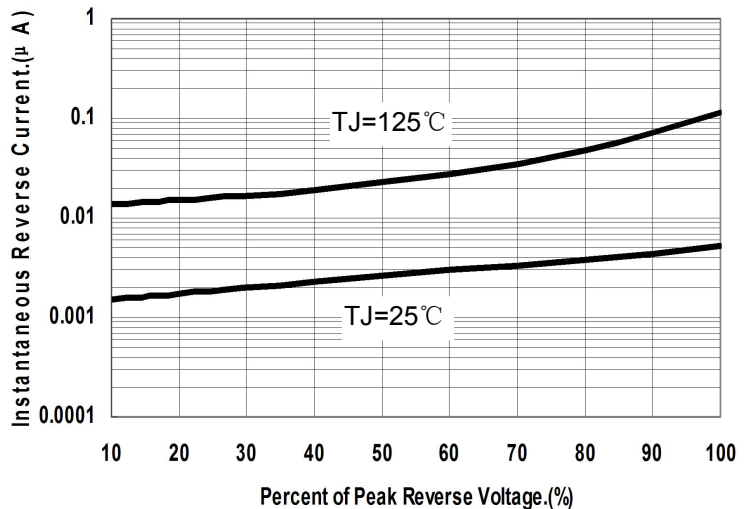


Fig.2-Typical Reverse Characteristics

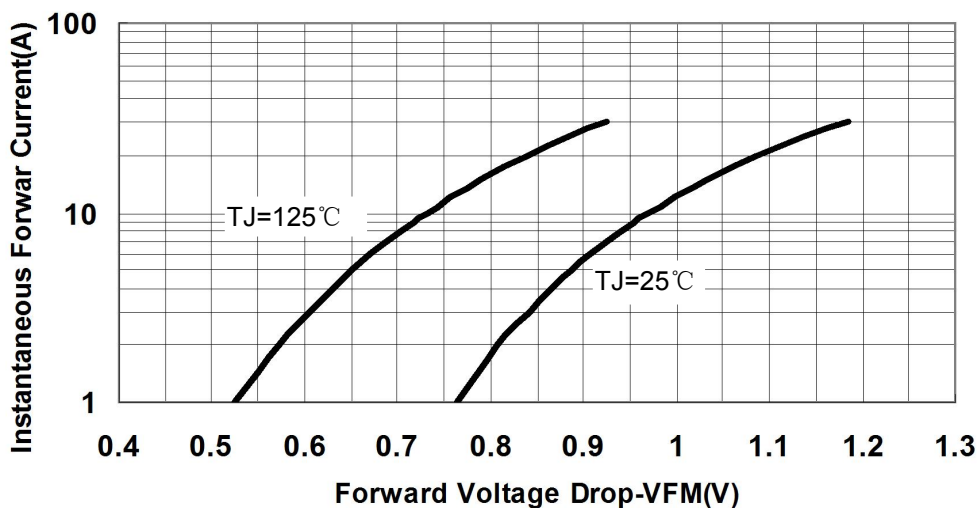
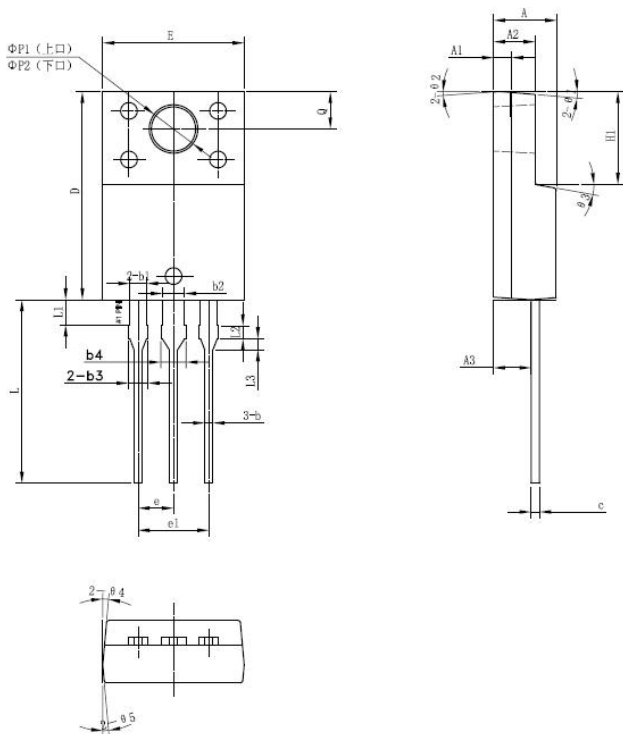
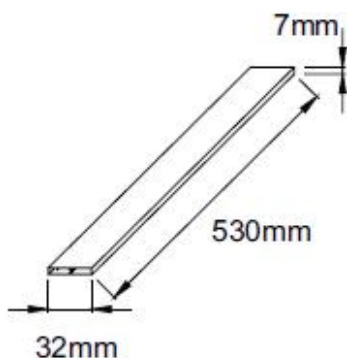
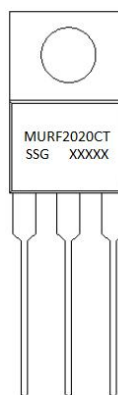


Fig.3-Typical Forward Voltage Drop Characteristics

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Mechanical Dimensions ITO-220AB


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上□)	3.30	3.50	3.70
ΦP2(下□)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Tube Specification

Marking Diagram


Where XXXXX is YYWWL

MUR = Device Type
 F = Package type
 20 = Forward Current (20A)
 20 = Reverse Voltage (200V)
 CT = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MURF2020CT	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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